

HiPerFRED

 $V_{RRM} = 1200 V$

 $I_{DAV} = 60 A$

 $t_{rr} = 60 \, \text{ns}$

High Performance Fast Recovery Diode Low Loss and Soft Recovery 1~ Rectifier Bridge

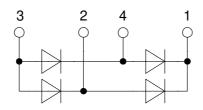
Part number

VBE60-12A



Backside: isolated





Features / Advantages:

- Planar passivated chips
- Very low leakage current
 Vary about reasons times.
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

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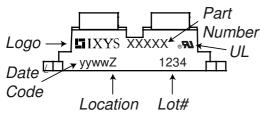


Fast Diode					Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blocki	ng voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
V_{RRM}	max. repetitive reverse blocking ve	oltage	$T_{VJ} = 25^{\circ}C$			1200	٧	
I _R	reverse current, drain current	V _R = 1200 V	$T_{VJ} = 25^{\circ}C$			250	μΑ	
		$V_R = 1200 \text{ V}$	$T_{VJ} = 125^{\circ}C$			1	mΑ	
V _F	forward voltage drop	I _F = 30 A	$T_{VJ} = 25^{\circ}C$			2.68	V	
		$I_F = 60 \text{ A}$				3.15	٧	
		I _F = 30 A	T _{VJ} = 150°C			1.73	V	
		$I_F = 60 \text{ A}$				2.22	٧	
I _{DAV}	bridge output current	T _C = 70°C	$T_{VJ} = 150$ °C			60	Α	
		rectangular d = 0.5					i 	
V _{F0}	threshold voltage		T _{VJ} = 150°C			1.31	٧	
r _F	slope resistance	ss calculation only				14	mΩ	
R _{thJC}	thermal resistance junction to case	9				1.15	K/W	
R _{thCH}	thermal resistance case to heatsin	k			0.1		K/W	
P _{tot}	total power dissipation		$T_{C} = 25^{\circ}C$			110	W	
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			200	Α	
CJ	junction capacitance	$V_R = 600 \text{V}$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		12		pF	
I _{RM}	max. reverse recovery current		$T_{VJ} = 25 ^{\circ}\text{C}$		8.5		Α	
		$I_F = 30 \text{ A}; V_R = 600 \text{ V}$	$T_{VJ} = 100 ^{\circ}\text{C}$		13		Α	
t _{rr}	reverse recovery time	$I_F = 30 \text{ A}; V_R = 600 \text{ V}$ -di _F /dt = 200 A/µs	$T_{VJ} = 25 ^{\circ}\text{C}$		60		ns	
	,	1	$T_{VJ} = 100^{\circ}C$		170		ns	



Package SOT-227B (minibloc)			Ratings					
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					150	Α
T _{VJ}	virtual junction temperatur	re			-40		150	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		150	°C
Weight						30		g
M _D	mounting torque				1.1		1.5	Nm
$\mathbf{M}_{_{T}}$	terminal torque				1.1		1.5	Nm
d _{Spp/App}	oroonaga diatanaa an auri	face Latriking diatance through air	terminal to terminal	10.5	3.2			mm
$d_{Spb/Apb}$	creepage distance on sun	face striking distance through air	terminal to backside	8.6	6.8			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		3000			٧
1002		t = 1 minute			2500			٧

Product Marking

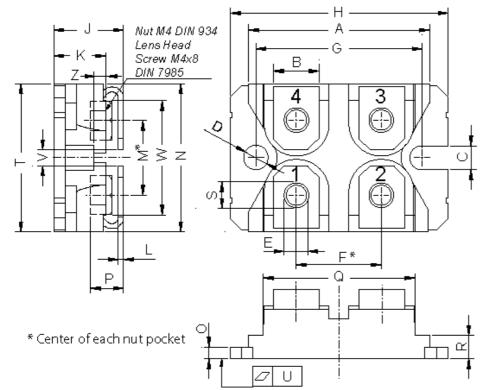


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VBE60-12A	VBE60-12A	Tube	10	514294

Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150^{\circ}C$
$I \rightarrow V_0$)—[R ₀]–	Fast Diode		
V _{0 max}	threshold voltage	1.31		V
R _{0 max}	slope resistance *	12		mΩ



Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches		
Dim.	min	max	min	max	
Α	31.50	31.88	1.240	1.255	
В	7.80	8.20	0.307	0.323	
С	4.09	4.29	0.161	0.169	
D	4.09	4.29	0.161	0.169	
Е	4.09	4.29	0.161	0.169	
F	14.91	15.11	0.587	0.595	
G	30.12	30.30	1.186	1.193	
Н	37.80	38.23	1.488	1.505	
J	11.68	12.22	0.460	0.481	
K	8.92	9.60	0.351	0.378	
L	0.74	0.84	0.029	0.033	
M	12.50	13.10	0.492	0.516	
N	25.15	25.42	0.990	1.001	
0	1.95	2.13	0.077	0.084	
Р	4.95	6.20	0.195	0.244	
Q	26.54	26.90	1.045	1.059	
R	3.94	4.42	0.155	0.167	
S	4.55	4.85	0.179	0.191	
Т	24.59	25.25	0.968	0.994	
U	-0.05	0.10	-0.002	0.004	
V	3.20	5.50	0.126	0.217	
W	19.81	21.08	0.780	0.830	
Ζ	2.50	2.70	0.098	0.106	

